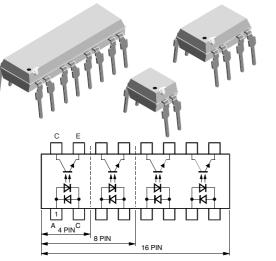
Vishay Semiconductors

Optocoupler, Phototransistor Output, AC Input



DESCRIPTION

17220 2

VISHA

The K814P/K824P/K844P consist of a phototransistor optically coupled to 2 gallium arsenide infrared emitting diodes (reverse polarity) in 4-pin (single); 8 pin (dual) or 16-pin (quad) plastic dual inline package.

The elements are mounted on one leadframe providing a fixed distance between input and output for highest safety requirements.

FEATURES

- · Endstackable to 2.54 mm (0.1") spacing
- DC isolation test voltage V_{ISO} = 5000 V_{RMS}
- Low coupling capacitance of typical 0.3 pF
- Current transfer ratio (CTR) of typical 100 %
- Low temperature coefficient of CTR
- Wide ambient temperature range
- · Lead (Pb)-free component
- · Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- · Feature phones
- · Answering machines
- 59 • PBX
- Fax machines

AGENCY APPROVALS

- UL1577, file no. E76222 system code U, double protection
- C-UL CSA 22.2, bulletin 5A

ORDER INFORMATION	
PART	REMARKS
K814P	CTR > 20 %, single channel, DIP-4
K824P	CTR > 20 %, dual channel, DIP-8
K844P	CTR > 20 %, quad channel, DIP-16

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT							
Forward current		I _F	± 60	mA			
Forward surge current	$t_P \le 10 \ \mu s$	I _{FSM}	± 1.5	А			
Power dissipation		P _{diss}	100	mW			
Junction temperature		Tj	125	°C			
OUTPUT							
Collector emitter voltage		V _{CEO}	70	V			
Emitter collector voltage		V _{ECO}	7	V			
Collector current		Ι _C	50	mA			
Collector peak current	$t_p/T=0.5,t_p\leq 10\ ms$	I _{CM}	100	mA			
Power dissipation		P _{diss}	150	mW			
Junction temperature		Tj	125	°C			





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ABSOLUTE MAXIMUM RATINGS ⁽¹⁾							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
COUPLER							
AC isolation test voltage (RMS)	t = 1.0 min	V _{ISO} ⁽²⁾	5000	V _{RMS}			
Total power dissipation		P _{tot}	250	mW			
Operating ambient temperature range		T _{amb}	- 40 to +100	°C			
Storage temperature range		T _{stg}	- 55 to + 125	°C			
Soldering temperature (3)	2 mm from case, t \leq 10 s	T _{sld}	260	°C			

Notes

⁽¹⁾ $T_{amb} = 25$ °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Related to standard climate 23/50 DIN 50014.

⁽³⁾ Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	I _F = ± 50 mA 🧼	V _F		1.25	1.6	V		
Reverse current	V _R = ± 6.0 V	I IR			10	μΑ		
OUTPUT								
Collector emitter voltage	I _C = 100 μA	♦ V _{CEO}	70			V		
Emitter collector voltage	l _E = 100 μA	V _{ECO}	7			V		
Collector dark current	$V_{CE} = 20 \text{ V}, \text{ I}_{F} = 0, \text{ E} = 0$	I _{CEO}			100	nA		
COUPLER								
Collector emitter saturation voltage	$I_{\rm F} = \pm 10 \text{ mA}, I_{\rm C} = 1 \text{ mA}$	V _{CEsat}			0.3	V		
Cut-off frequency	$I_{F} = \pm 10 \text{ mA}, \text{ V}_{CE} = 5 \text{ V},$ $R_{L} = 100 \Omega$	f _c		100		kHz		
Coupling capacitance	f = 1 MHz	C _k		0.3		pF		

Note

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANS	FER RATIO						
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I _C /I _F	$V_{CE} = 5 \text{ V}, \text{ I}_{F} = \pm 5 \text{ mA}$	K814P	CTR	20		300	%

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}, \text{ R}_{L} = 100 \Omega \text{ (see figure 1)}$	t _d		3.0		μs
Rise time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}, \text{ R}_{L} = 100 \Omega \text{ (see figure 1)}$	t _r		3.0		μs
Fall time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}, \text{ R}_{L} = 100 \Omega \text{ (see figure 1)}$	t _f		4.7		μs
Storage time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}, \text{ R}_{L} = 100 \Omega \text{ (see figure 1)}$	ts		0.3		μs
Turn-on time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}, \text{ R}_{L} = 100 \Omega \text{ (see figure 1)}$	t _{on}		6.0		μs
Turn-off time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}, \text{ R}_{L} = 100 \Omega \text{ (see figure 1)}$	t _{off}		5.0		μs
Turn-on time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 10 \text{ mA}, \text{ R}_{L} = 1 \text{ k}\Omega \text{ (see figure 1)}$	t _{on}		9.0		μs
Turn-off time	$V_S = 5 \text{ V}, \text{ I}_C = 10 \text{ mA}, \text{ R}_L = 1 \text{ k}\Omega \text{ (see figure 1)}$	t _{off}		18.0		μs

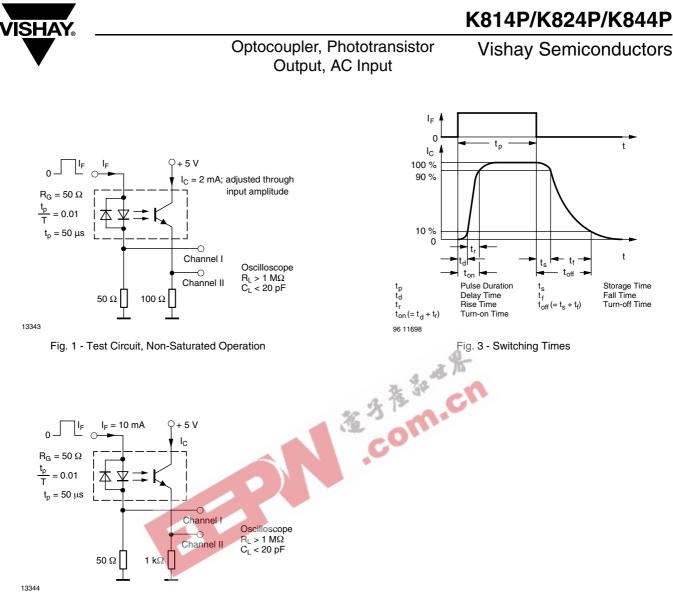
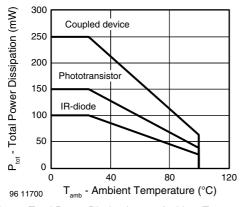


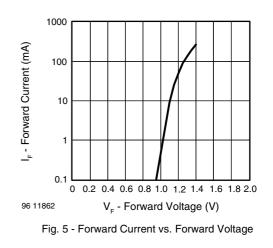
Fig. 2 - Test Circuit, Saturated Operation

TYPICAL CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

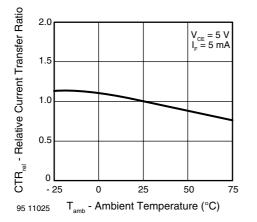






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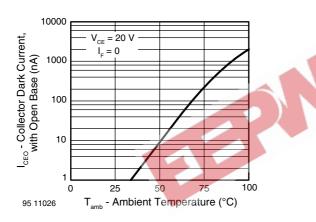


Fig. 7 - Collector Dark Current vs. Ambient Temperature

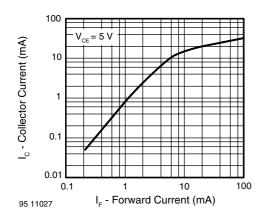
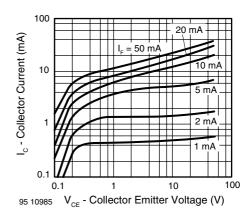
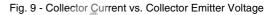


Fig. 8 - Collector Current vs. Forward Current



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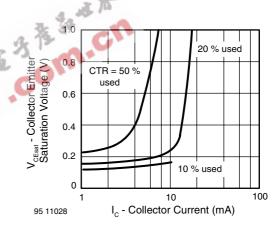


Fig. 10 - Collector Emitter Saturation Voltage vs. Collector Current

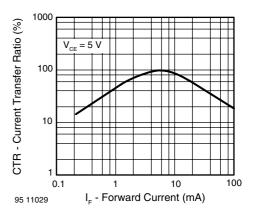
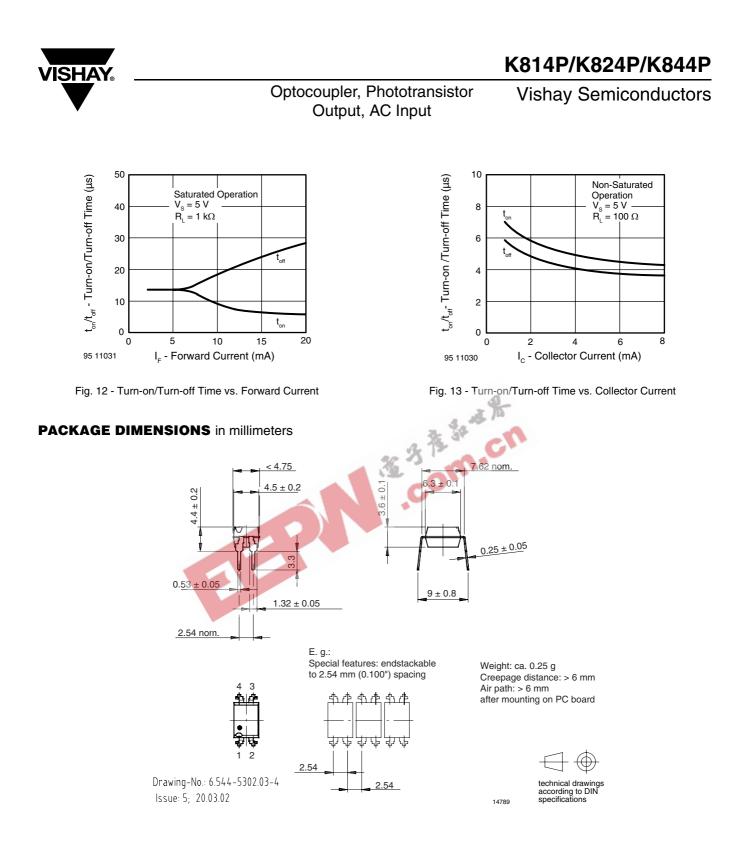


Fig. 11 - Current Transfer Ratio vs. Forward Current



K814P/K824P/K844P **VISHAY**® Optocoupler, Phototransistor **Vishay Semiconductors** Output, AC Input < 20 7.62 nom. 3.6 ± 0.1 4.4 ± 0.2 19.7 ± 0.2 6.3 ± 0.1 3.3 0.25 ± 0.05 0.53 ± 0.05 9 ± 0.8 1.32 ± 0.05 2.54 nom. 7 x 2.54 = 17.78 Weight: ca. 1.08 g Creepage distance: > 6 mm technical drawi according to DIN specifications Air path: > 6 mm 16 15 14 13 12 11 10 9 after mounting on PC board ጭ <u>ቆጓቆጓቆቅ</u> Drawing-No.: 6.544-5302.01 14783 5 ₽ ų, Issue: 4; 02.06.99 7 1 2 3 4 5 6 8 < 9.8 7.62 nom. 9.5 ± 0.2 3.6 ± 0.1 6.3 ± 0.1 $.4 \pm 0.2$ 0.25 ± 0.05 3.3 0.53 ± 0.05 9 ± 0.8 1.32 ± 0.05 2.54 nom. Weight: ca. 0.55 g 3 x 2.54 = 7.62 technical drawings according to DIN specifications Creepage distance: > 6 mm Air path: > 6 mm 6 5 after mounting on PC board

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Drawing-No.: 6.544-5302.02-4

Issue: 4; 02.06.99

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Optocoupler, Phototransistor Output, AC Input

Vishay Semiconductors

OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Vishay

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